

SC141

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Repetitive peak off-stage voltage, gate open			
SC141A		100	
SC141B		200	
SC141D	V_{DRM}	400	Volts
SC141E		500	
SC141M		600	
SC141N		700	
RMS on-state current (T _C = 80°C)	I _{T(RMS)}	6	Amps
Peak non-repetitive surge current (One Cycle, 60Hz)	I _{TSM}	80	Amps
Circuit fusing considerations	l ² t		A ² s
(t = 8.3ms)	11	26.5	AS
Peak gate power (pulse width = 10μs)	P _{GM}	10	Watts
Average gate power (T _C = 80°C, t = 8.3ms)	P _{G(AV)}	0.5	Watts
Peak gate current (pulse width = 10μs)	I _{GM}	3.5	Amps
Peak gate voltage	V _{GM}	10	Volts
Operating junction temperature range	T _J	-40 to +100	°C
Storage temperature range	T _{stg}	-40 to +125	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal resistance, junction to case	$R_{\Theta JC}$	2.2	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak off state current					
(V _D = V _{DRM} , gate open)					mA
T _C = 25°C	I _{DRM}	-	-	0.1	IIIA
T _C = 110°C		-	-	0.5	
Peak on-state voltage	\/				Volts
$(I_{TM} = 8.5 \text{A peak, pulse width} \le 1 \text{ ms, duty cycle} \le 2\%)$	V _{TM}	-	-	1.83	VOILS
Critical rate of rise of off-state voltage					1//
$(V_D = Rated V_{DRM}, gate open, exponential waveform, T_C = 100°C)$	dv/dt	-	50	-	V/µs
Critical rate of rise of commutating voltage					
($I_{T(RMS)}$ = Rated $I_{T(RMS)}$, V_D = Rated V_{DRM} , commutating di/dt = 3.2A/ms, gate open, T_C = 80°C)	dv/dt(c)	4	-	-	V/µs



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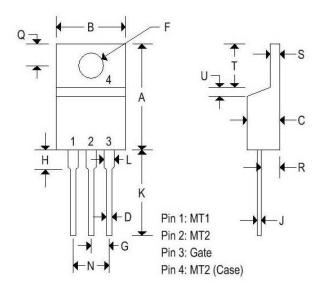
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DC gate trigger current (continuous dc)					
(V _D = 12V, trigger mode)					
MT2(+), G(+); MT2(-), G(-); $R_L = 100\Omega$		-	-	50	mA
MT2(+), G(-); $R_L = 50\Omega$	I _{GT}	-	-	50	IIIA
MT2(+), G(+); MT2(-), G(-); $R_L = 50\Omega$, $T_C = -40^{\circ}C$		-	-	80	
MT2(+), G(-); $R_L = 25\Omega$, $T_C = -40^{\circ}C$		-	-	80	
DC gate trigger voltage (continuous dc)					
(V _D = 12V, trigger mode)					
MT2(+), G(+); MT2(-), G(-); $R_L = 100\Omega$		-	-	2.5	
$MT2(+), G(-); R_L = 50\Omega$	V_{GT}	-	-	2.5	Volts
MT2(+), G(+); MT2(-), G(-); $R_L = 50\Omega$, $T_C = -40^{\circ}C$		-	-	3.5	
MT2(+), G(-); $R_L = 25\Omega$, $T_C = -40^{\circ}C$		-	-	3.5	
(V_D = Rated V_{DRM} , R_L = 1000 Ω , T_C = 100°C) all polarities		0.2	-	-	
Holding current	I _H				mA
$(V_D = 24V, I_T = 0.5A, pulse width = 1ms, duty cycle \le 2\%,$					
gate trigger source 7V, 20Ω)					
T _C = 25°C		-	-	50	
$T_C = -40^{\circ}C$		-	-	100	
Latching current	IL				mA
(V _D = 24V)					
Trigger source: 15V, 100Ω , trigger mode)					
MT2(+), G(+); MT2(-), G(-)		-	-	100	
MT2(+), G(-)		-	-	200	
MT2(+), G(+); MT2(-), G(-), $T_c = -40^{\circ}C$		-	-	200	
MT2(+), G(-), $T_c = -40$ °C		-		400	



MECHANICAL CHARACTERISTICS

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below



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	TO-220AB					
	Inc	Inches		Millimeters		
	Min	Max	Min	Max		
Α	0.575	0.620	14.600	15.750		
В	0.380	0.405	9.650	10.290		
С	0.160	0.190	4.060	4.820		
D	0.025	0.035	0.640	0.890		
F	0.142	0.147	3.610	3.730		
G	0.095	0.105	2.410	2.670		
Н	0.110	0.155	2.790	3.930		
J	0.014	0.022	0.360	0.560		
K	0.500	0.562	12.700	14.270		
L	0.045	0.055	1.140	1.390		
N	0.190	0.210	4.830	5.330		
Q	0.100	0.120	2.540	3.040		
R	0.080	0.110	2.040	2.790		
S	0.045	0.055	1.140	1.390		
T	0.235	0.255	5.970	6.480		
U	14	0.050	97	1.270		
٧	0.045	0.0	1.140	(2)		
Z	-	0.080	121	2.030		



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